



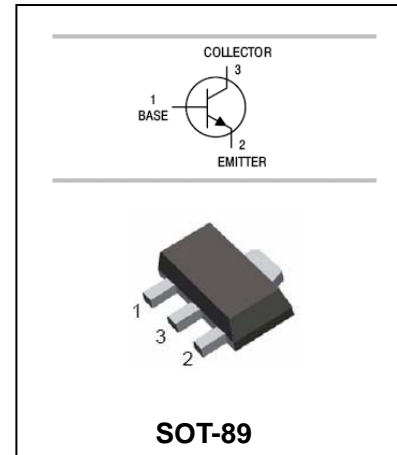
DONGGUAN NANJING ELECTRONICS LTD.,

**NPN Silicon Epitaxial Planar Transistor**

**2SC2884**

**FEATURES**

- Suitable for output stage of 1 watts amplifier.
- High DC current gain.
- Small flat package.
- $P_C=1.0$  to  $2.0W$ .
- Complements the 2SA1204.



**ORDERING INFORMATION**

Type No.	Marking	Package Code
2SC2884	PO1/PY1	SOT-89

**MAXIMUM RATING @  $T_a=25^{\circ}C$  unless otherwise specified**

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	35	V
$V_{CEO}$	Collector-Emitter Voltage	30	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	0.8	A
$I_B$	Base Current	0.16	A
$P_C$	Collector Dissipation	500	mW
$T_j, T_{stg}$	Junction and Storage Temperature	-55 to +150	$^{\circ}C$

# NPN Silicon Epitaxial Planar Transistor

# 2SC2884

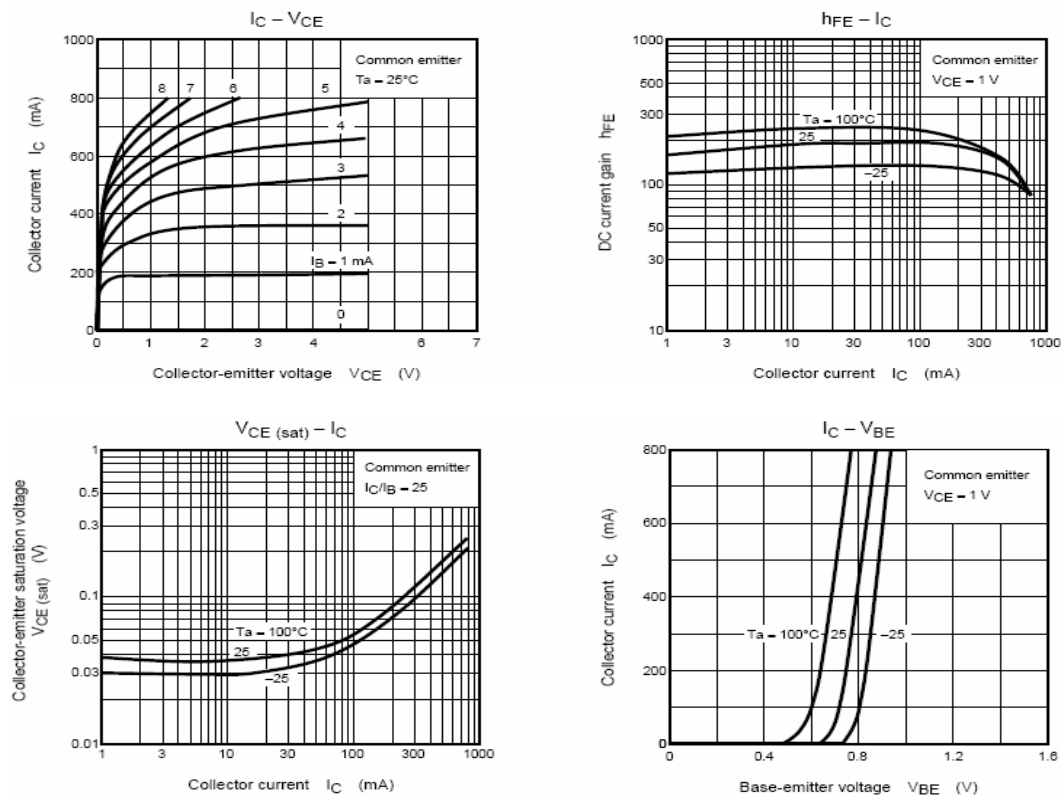
## ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	30			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=35V, I_E=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=1V, I_C=100mA$	100		320	
		$V_{CE}=1V, I_C=700mA$	35			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=0.5A, I_B=0.02A$			0.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=1V, I_C=10mA$	0.5		0.8	V
Transition frequency	$f_T$	$V_{CE}=5V, I_C=10mA$		120		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$		13		pF

## CLASSIFICATION OF $h_{FE}$

Rank	O	Y
Range	100-200	160-320
MARKING	PO1	PY1

## TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



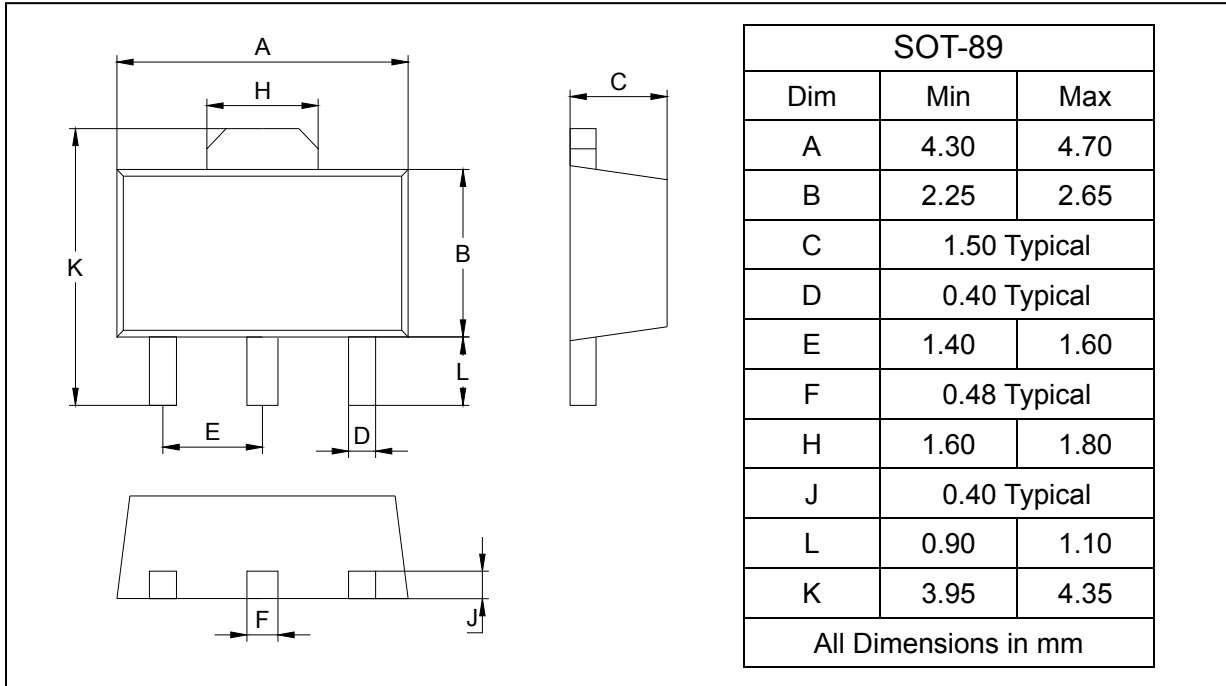
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**2SC2884**

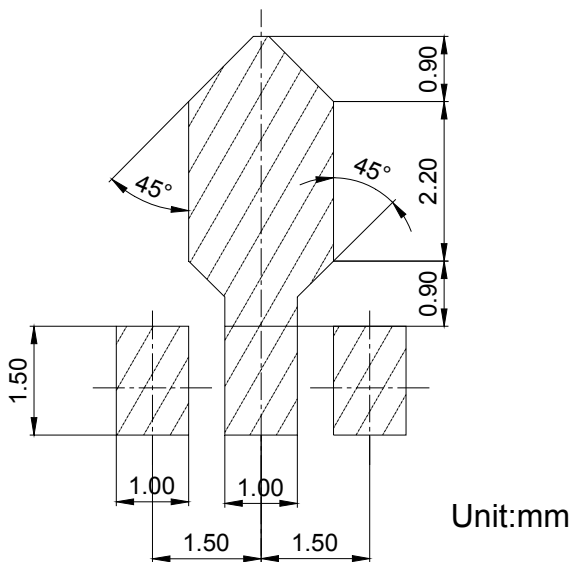
## PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



## SOLDERING FOOTPRINT



## PACKAGE INFORMATION

Device	Package	Shipping
2SC2884	SOT-89	1000/Tape&Reel